Low Noise Transistors

NPN Silicon

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT5088L MMBT5089L	V _{CEO}	30 25	Vdc
Collector – Base Voltage MMBT5088L MMBT5089L	V _{CBO}	35 30	Vdc
Emitter-Base Voltage	V _{EBO}	4.5	Vdc
Collector Current – Continuous	Ι _C	50	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

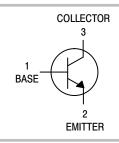


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SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



1x = Device Code x = Q for MMBT5088L

- SMMBT5088L
- x = R for MMBT5089L
- SMMBT5089L
- M = Date Code*
- = Pb–Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT5088LT1G,	SOT-23	3,000 / Tape &
SMMBT5088LT1G	(Pb-Free)	Reel
NSVMMBT5088LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT5089LT1G,	SOT-23	3,000 / Tape &
SMMBT5089LT1G	(Pb-Free)	Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•	
Collector – Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBT5088L MMBT5089L	V _{(BR)CEO}	30 25		Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	MMBT5088L MMBT5089L	V _{(BR)CBO}	35 30		Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 15 \text{ Vdc}, I_E = 0)$	MMBT5088L MMBT5089L	I _{CBO}	- -	50 50	nAdc
$\begin{array}{l} \mbox{Emitter Cutoff Current} \\ (V_{EB(off)} = 3.0 \mbox{ Vdc}, \mbox{ I}_{C} = 0) \\ (V_{EB(off)} = 4.5 \mbox{ Vdc}, \mbox{ I}_{C} = 0) \end{array}$	MMBT5088L MMBT5089L	I _{EBO}	- -	50 100	nAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc)	MMBT5088L MMBT5089L	h _{FE}	300 400	900 1200	-
$(I_{C} = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT5088L MMBT5089L		350 450		
$(I_{C} = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT5088L MMBT5089L		300 400		
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$)		V _{CE(sat)}	_	0.5	Vdc
Base – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$)		V _{BE(sat)}	_	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product ($I_C = 500 \ \mu Adc$, $V_{CE} = 5.0 \ Vdc$, f = 20 MHz)		f _T	50	_	MHz
Collector–Base Capacitance ($V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$ emitter guarded)		C _{cb}	_	4.0	pF
Emitter–Base Capacitance (V_{EB} = 0.5 Vdc, I_{C} = 0, f = 1.0 MHz collector guarded)		C _{eb}	-	10	pF
Small Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	MMBT5088L MMBT5089L	h _{fe}	350 450	1400 1800	_
Noise Figure (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 10 kΩ, f = 1.0 kHz)	MMBT5088L MMBT5089L	NF	-	3.0 2.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

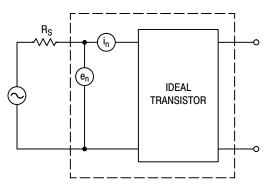
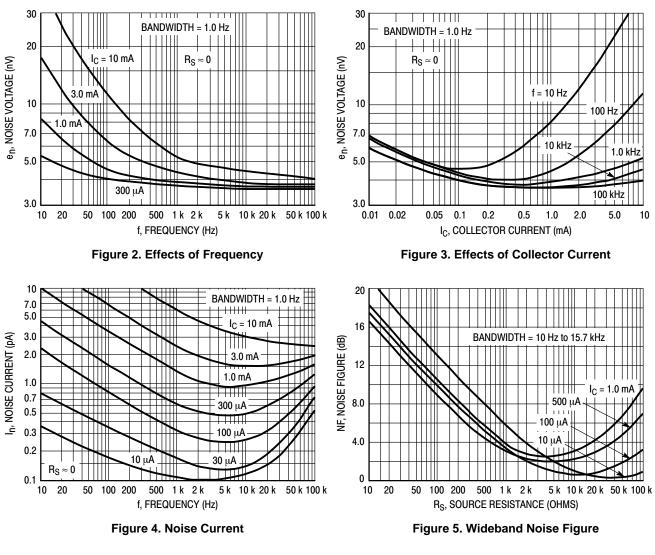


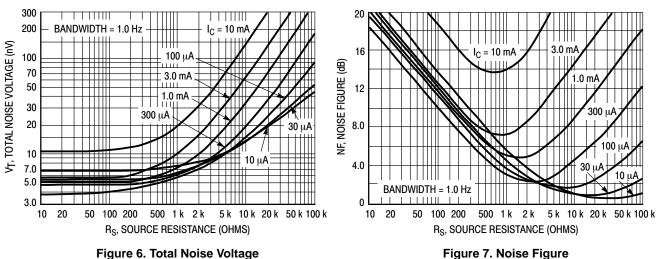
Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

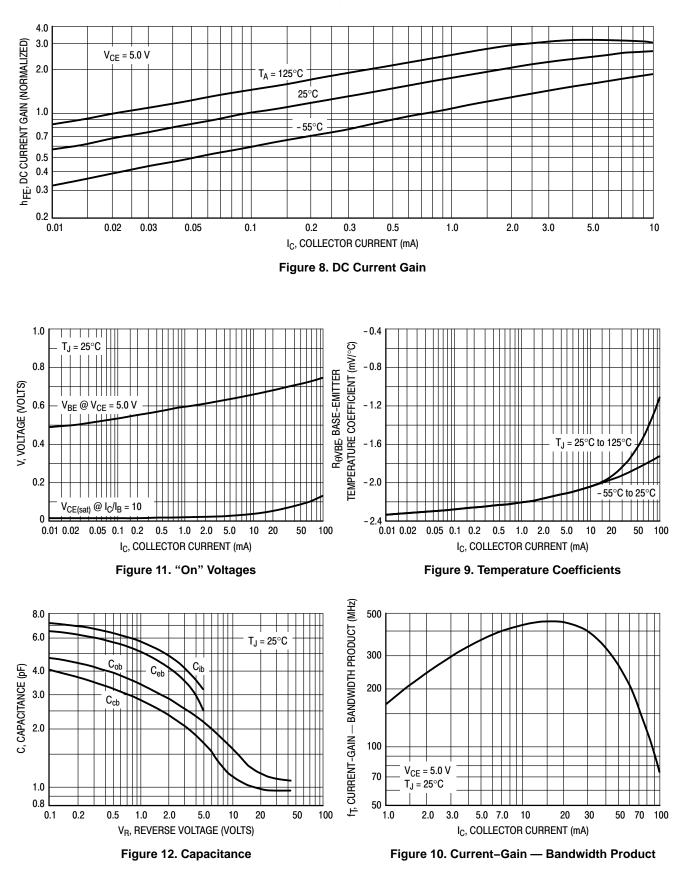
NOISE VOLTAGE





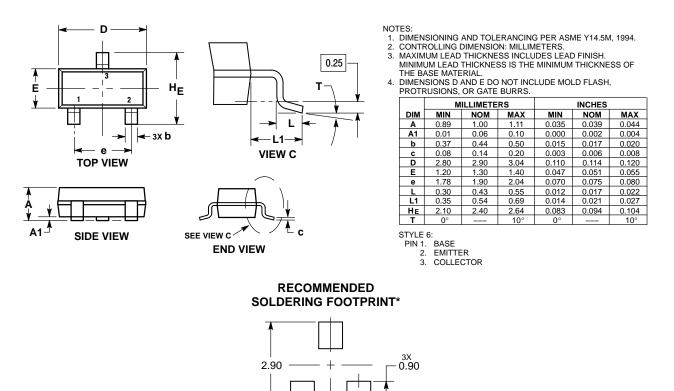
100 Hz NOISE DATA

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PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AR



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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